





#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

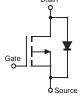
#### **Features**

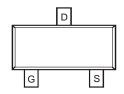
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 3)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)







Top View

**Equivalent Circuit** 

Top View

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-50	V	
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		$V_{DGR}$	-50	V	
Gate-Source Voltage	Continuous	$V_{GSS}$	±20	V	
Drain Current (Note 1)	Continuous	I <sub>D</sub>	-130	mA	
Pulsed Drain Current		I <sub>DM</sub>	-1.2	А	

### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_{D}$	300	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 2)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
		_	_	-15	μΑ	$V_{DS} = -50V, V_{GS} = 0V, T_{J} = 25^{\circ}C$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-60	μA	$V_{DS} = -50V$ , $V_{GS} = 0V$ , $T_{J} = 125$ °C	
		—		-100	nΑ	$V_{DS} = -25V, V_{GS} = 0V, T_{J} = 25^{\circ}C$	
Gate-Body Leakage	I <sub>GSS</sub>	_		±10	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.8		-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	_	10	Ω	$V_{GS} = -5V, I_D = -0.100A$	
Forward Transconductance	g <sub>FS</sub>	0.05	_	_	S	$V_{DS} = -25V, I_{D} = -0.1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	_	_	45	pF		
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	12	pF		
SWITCHING CHARACTERISTICS	•						
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10	_	ns	$V_{DD} = -30V$ , $I_D = -0.27A$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18	_	ns	$R_{GEN} = 50\Omega$ , $V_{GS} = -10V$	

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. Short duration pulse test used to minimize self-heating effect.
- 3. No purposefully added lead. Halogen and Antimony Free.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.



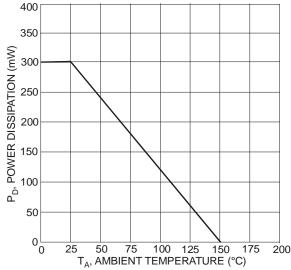
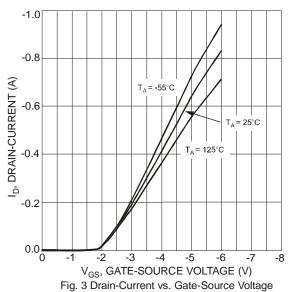


Fig. 1 Max Power Dissipation vs. Ambient Temperature



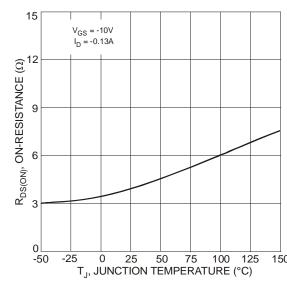


Fig. 5 On-Resistance vs. Junction Temperature

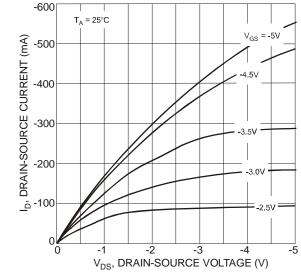


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

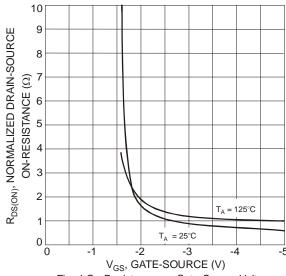


Fig. 4 On-Resistance vs. Gate-Source Voltage

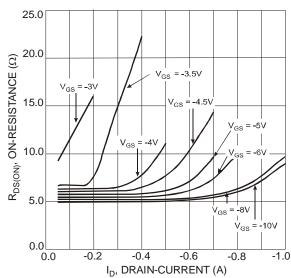


Fig. 6 On-Resistance vs. Drain-Current

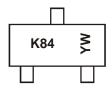


## Ordering Information (Note 5)

Part Number	Case	Packaging
BSS84-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

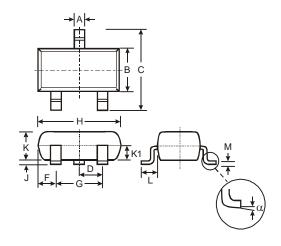


K84 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Kev

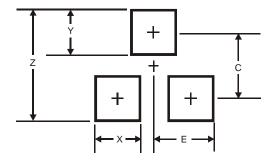
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Χ	Υ	Z
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D

# **Package Outline Dimensions**



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	•	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

#### **LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2010, Diodes Incorporated

www.diodes.com